

# 제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

## K. Memory (Design & Process Technology) 분과

Room J  
청옥 I (6층)

2016년 2월 23일(화) 15:10-17:10

[TJ3-K] Circuit Related Topics and Memory Selectors

좌장 : 김택승(SK 하이닉스), 이중호(용인대학교)

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| TJ3-K-1 | 15:10-15:25 | <b>Origin of Leakage Current of NbO<sub>x</sub> Film and Improved Threshold Switching Characteristics of Multi-layer NbO<sub>x</sub> Selector</b><br>JaeHyuk Park, Euijun Cha, Sangheon Lee, Jeonghwan Song, Jaesung Park, and Hyunsang Hwang<br><i>Department of MS&amp;E, Pohang University of Science and Technology</i>   |
| TJ3-K-2 | 15:25-15:55 | <b>[초청] Neuromorphic Crossbar Circuits of Memristors</b><br>송재상, Son Ngoc Truong, 양원선, 민경식<br><i>국민대학교 전자공학부</i>  |
| TJ3-K-3 | 15:55-16:10 | <b>Double Layer-Stacked 1D1R Crossbar Array Integrating Diode Selector with Rectification Ratio of ~10<sup>9</sup></b><br>Kyung Jean Yoon, Yeong Jae Kwon, Sijung Yoo, Jung Ho Yoon, Hye Jin Kim, Dae Eun Kwon, Seul Ji Song, Tae Hyung Park, and Cheol Seong Hwang<br><i>Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University</i> |
| TJ3-K-4 | 16:10-16:25 | <b>결함 지도를 이용한 직교 라틴 방진 부호 기반의 저전력 메모리</b><br>김동현, 양준성<br><i>성균관대학교 반도체디스플레이공학과</i>  |
| TJ3-K-5 | 16:25-16:40 | <b>Design of Embedded ReRAM Macros for 40nm Logic Process</b><br>Yong-Seop Lee <sup>1</sup> , Soo-Gil Kim <sup>2</sup> , Do-Hee Kim <sup>1</sup> , and Sung-Kun Park <sup>1</sup><br><sup>1</sup> System IC Platform Technology Development Team, SK hynix Inc.,<br><sup>2</sup> NM Process Development Group, SK hynix Inc.  |
| TJ3-K-6 | 16:40-16:55 | <b>A Scalable Memory Array Architecture for Restricted Boltzmann Machines</b><br>Yunju Choi, Seung-Heon Baek, and Jaeha Kim<br><i>Department of Electrical and Computer Engineering, Seoul National University</i>  |
| TJ3-K-7 | 16:55-17:10 | <b>Performance Improvement of ReRAM Device using Low Temperature Silicon Nitride Spacer</b><br>Jong Chul Lee, Hyo June Kim, Sung Kyu Min, Ja Chun Ku, Soo Gil Kim, and Hyeong Soo Kim<br><i>New Memory process development Team, R&amp;D Division SK hynix Inc.</i>   |